MMBT2369LT1, MMBT2369ALT1

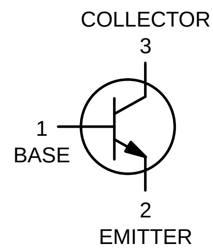
MMBT2369ALT1 is a Preferred Device

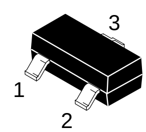
Switching Transistors

NPN Silicon

ON Semiconductor®

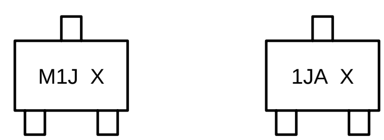
http://onsemi.com





SOT–23
CASE 318
STYLE 6

MARKING DIAGRAMS



MMBT2369LT1 MMBT2369ALT1

M1J, 1JA = Specific Device Code
X = Date Code

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	15	Vdc
Collector–Emitter Voltage	V_{CES}	40	Vdc
Collector–Base Voltage	V_{CBO}	40	Vdc
Emitter–Base Voltage	V_{EBO}	4.5	Vdc
Collector Current – Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

1. FR–5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

ORDERING INFORMATION

Device	Package	Shipping
MMBT2369LT1	SOT–23	3000/Tape & Reel
MMBT2369ALT1	SOT–23	3000/Tape & Reel

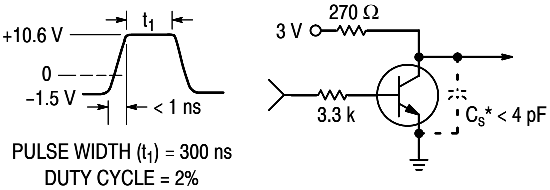
Preferred devices are recommended choices for future use and best overall value.

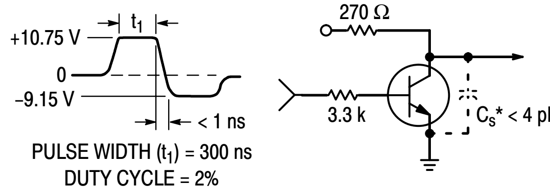
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (Note 3) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	15	–	–	Vdc
Collector–Emitter Breakdown Voltage (I_C = 10 μAdc, V_{BE} = 0)		$V_{(BR)CES}$	40	–	–	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	40	–	–	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.5	–	–	Vdc
Collector Cutoff Current		I_{CBO}				μAdc
(V_{CB} = 20 Vdc, I_E = 0)			–	–	0.4	
(V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)			–	–	30	
Collector Cutoff Current (V_{CE} = 20 Vdc, V_{BE} = 0)	MMBT2369A	I_{CES}	–	–	0.4	μAdc
ON CHARACTERISTICS						
DC Current Gain (Note 3)		h_{FE}				–
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	MMBT2369		40	–	120	
(I_C = 10 mAdc, V_{CE} = 1.0 Vdc)	MMBT2369A		–	–	120	
(I_C = 10 mAdc, V_{CE} = 0.35 Vdc)	MMBT2369A		40	–	–	
(I_C = 10 mAdc, V_{CE} = 0.35 Vdc, T_A = –55°C)	MMBT2369A		20	–	–	
(I_C = 30 mAdc, V_{CE} = 0.4 Vdc)	MMBT2369A		30	–	–	
(I_C = 100 mAdc, V_{CE} = 2.0 Vdc)	MMBT2369		20	–	–	
(I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	MMBT2369A		20	–	–	
Collector–Emitter Saturation Voltage (Note 3)		$V_{CE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	MMBT2369		–	–	0.25	
(I_C = 10 mAdc, I_B = 1.0 mAdc)	MMBT2369A		–	–	0.20	
(I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = +125°C)	MMBT2369A		–	–	0.30	
(I_C = 30 mAdc, I_B = 3.0 mAdc)	MMBT2369A		–	–	0.25	
(I_C = 100 mAdc, I_B = 10 mAdc)	MMBT2369A		–	–	0.50	
Base–Emitter Saturation Voltage (Note 3)		$V_{BE(sat)}$				Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)	MMBT2369A		0.7	–	0.85	
(I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = –55°C)	MMBT2369A		–	–	1.02	
(I_C = 30 mAdc, I_B = 3.0 mAdc)	MMBT2369A		–	–	1.15	
(I_C = 100 mAdc, I_B = 10 mAdc)	MMBT2369A		–	–	1.60	
SMALL–SIGNAL CHARACTERISTICS						
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	–	–	4.0	pF
Small Signal CurrentGain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		h_{fe}	5.0	–	–	–
SWITCHING CHARACTERISTICS						
Storage Time (I_{B1} = I_{B2} = I_C = 10 mAdc)		t_s	–	5.0	13	ns
Turn–On Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc)		t_{on}	–	8.0	12	ns
Turn–Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)		t_{off}	–	10	18	ns

3. Pulse Test: Pulse Width $\leq$ 300 μs, Duty Cycle $\leq$ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS FOR 2N2369, 2N3227

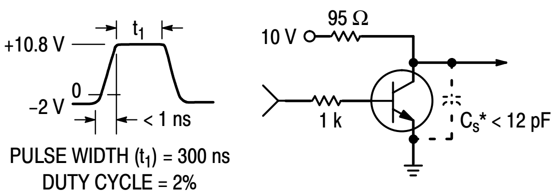


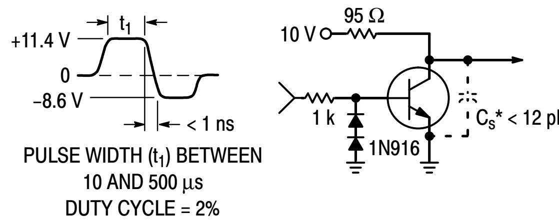


*Total shunt capacitance of test jig and connectors.

Figure 1. t_{on} Circuit – 10 mA

Figure 3. t_{off} Circuit – 10 mA





*Total shunt capacitance of test jig and connectors.

Figure 2. t_{on} Circuit – 100 mA

Figure 4. t_{off} Circuit – 100 mA

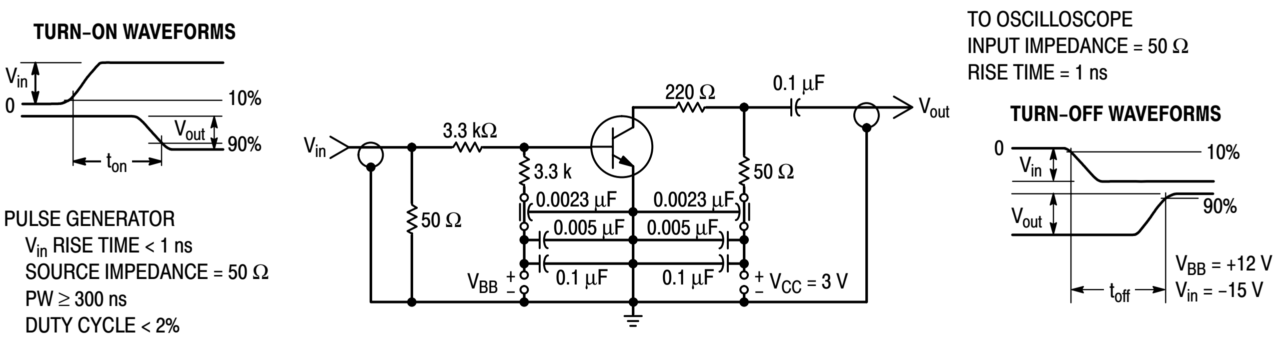


Figure 5. Turn–On and Turn–Off Time Test Circuit

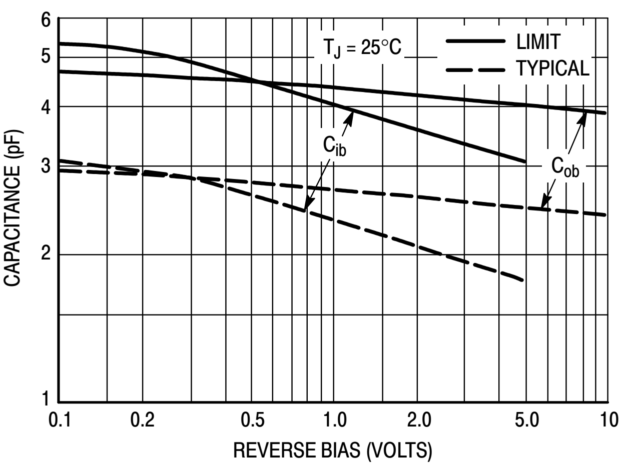


Figure 6. Junction Capacitance Variations

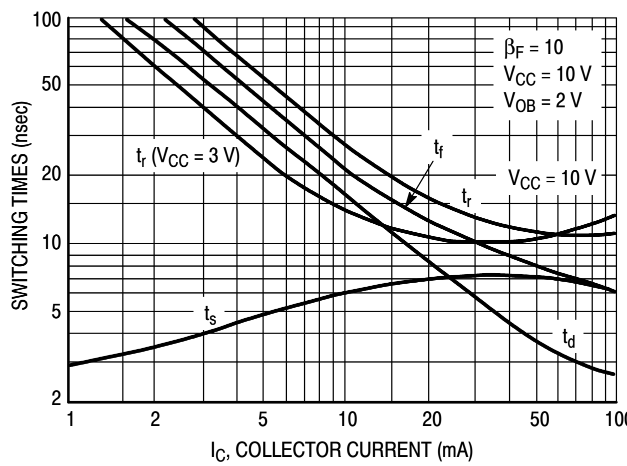


Figure 7. Typical Switching Times

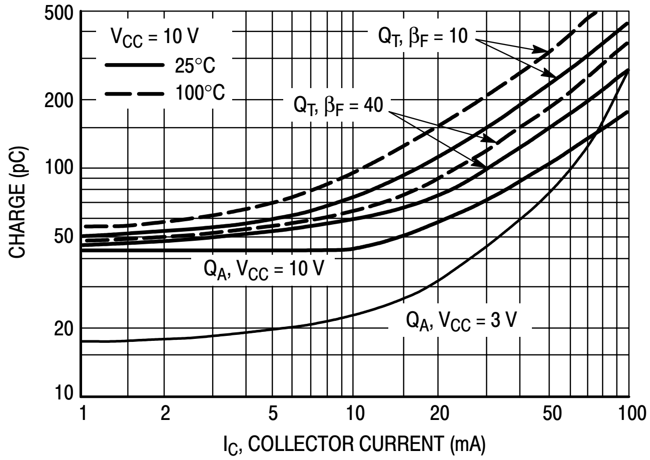


Figure 8. Maximum Charge Data

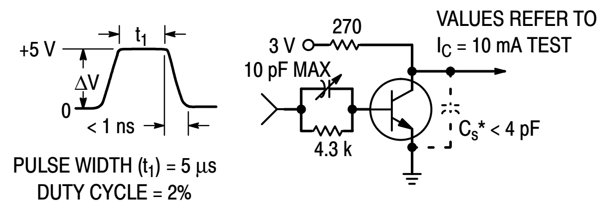


Figure 9. Q_T Test Circuit

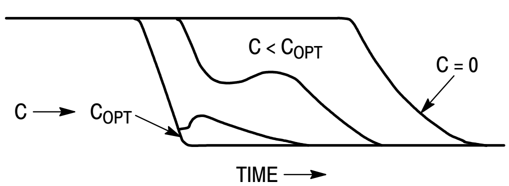


Figure 10. Turn–Off Waveform

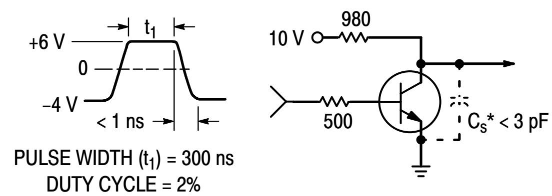


Figure 11. Storage Time Equivalent Test Circuit

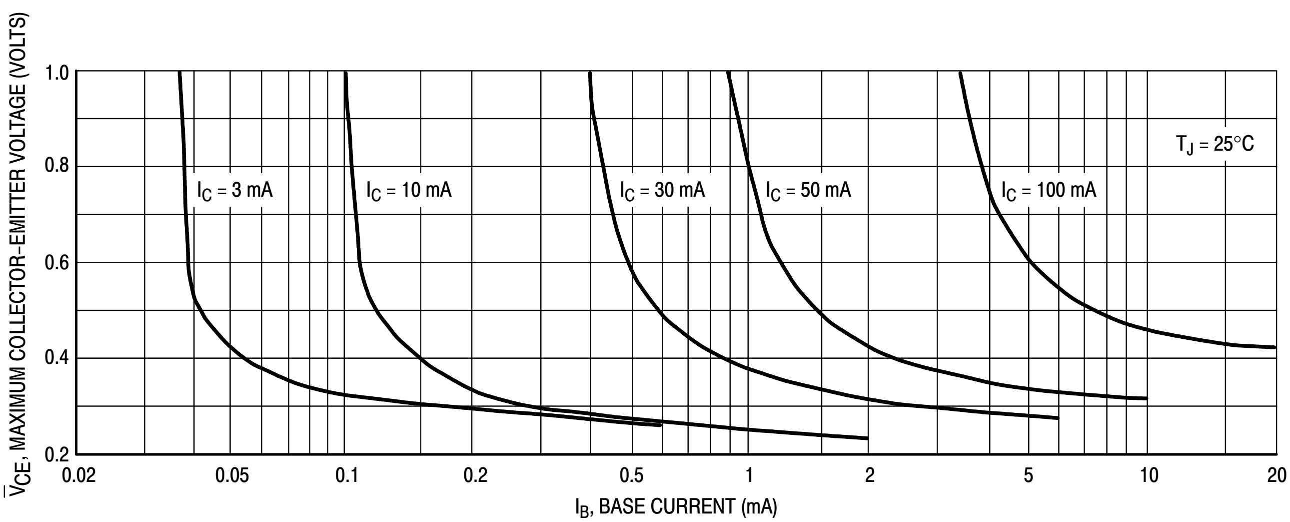


Figure 12. Maximum Collector Saturation Voltage Characteristics

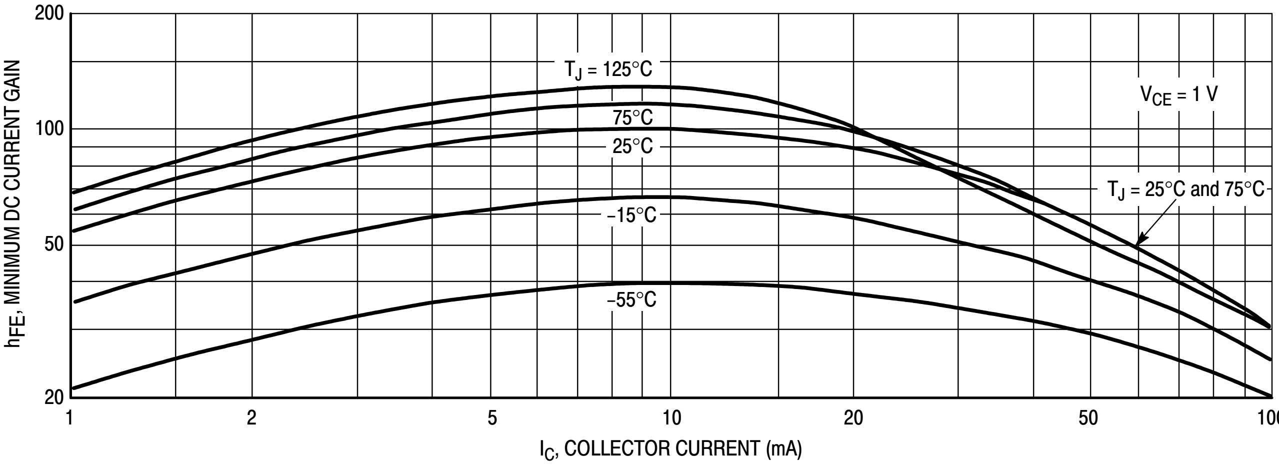


Figure 13. Minimum Current Gain Characteristics

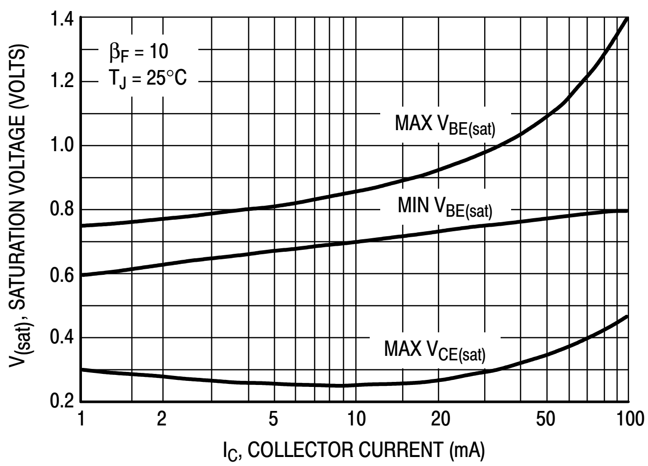
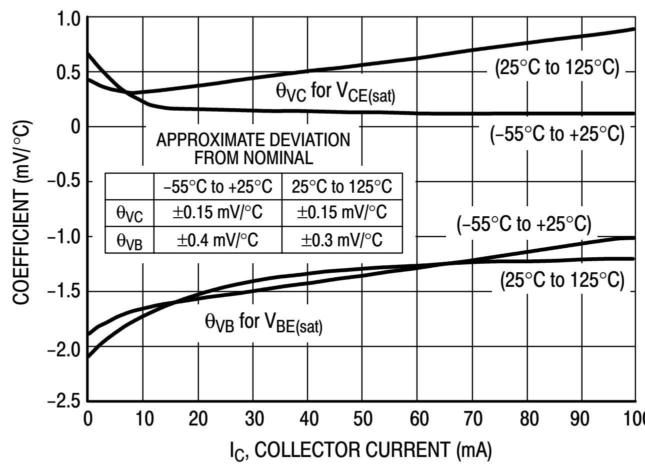


Figure 14. Saturation Voltage Limits



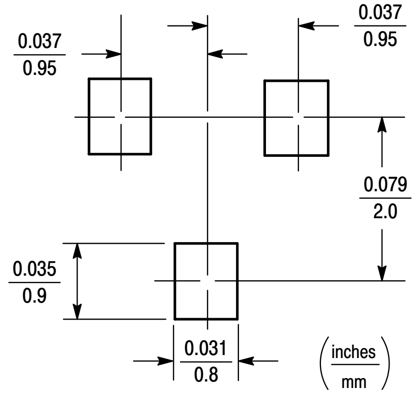
	−55°C to +25°C	25°C to 125°C
θ_{VC}	±0.15 mV/°C	±0.15 mV/°C
θ_{VB}	±0.4 mV/°C	±0.3 mV/°C

Figure 15. Typical Temperature Coefficients

INFORMATION FOR USING THE SOT–23 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



SOT–23

SOT–23 POWER DISSIPATION

The power dissipation of the SOT–23 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A. Using the values provided on the data sheet for the SOT–23 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_D = \frac{150°C - 25°C}{556°C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT–23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT–23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad®. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

SOLDERING PRECAUTIONS

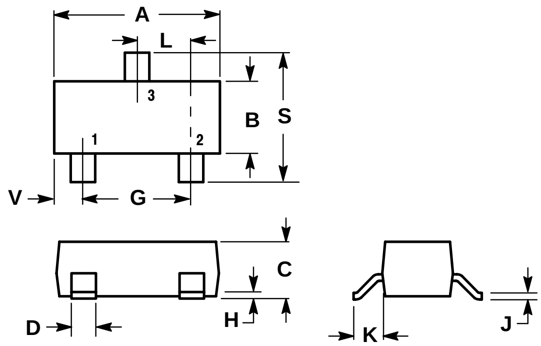
The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

PACKAGE DIMENSIONS

SOT–23 (TO–236)
CASE 318–08
ISSUE AH



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318–03 AND –07 OBSOLETE, NEW STANDARD 318–08.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

Thermal Clad is a registered trademark of the Bergquist Company.

PUBLICATION ORDERING INFORMATION

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